Andrzej Mazurak

List of Publications by Year
in descending order

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19	50	1937685 4	1720034 7
papers	citations	h-index	g-index

19	19	19	20
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Investigation of the anomalous effect of the AC-signal frequency on flat-band voltage of Al/HfO2/SiO2/Si structures. Solid-State Electronics, 2021, 183, 108107.	1.4	0
2	Investigation of Electrical Properties of the Al/SiO2/n++-Si Resistive Switching Structures by Means of Static, Admittance, and Impedance Spectroscopy Measurements. Materials, 2021, 14, 6042.	2.9	8
3	Silicon-Carbide (SiC) Nanocrystal Technology and Characterization and Its Applications in Memory Structures. Nanomaterials, 2020, 10, 2387.	4.1	8
4	Frequency Modulated C-V Characteristics Shift in Double-layer High-k Gate Stack MIS Devices. , 2020, , .		1
5	Determination of border/bulk traps parameters based on (<i>C</i>-<i>G</i>-<i>V</i>) admittance measurements. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2019, 37, .	1.2	2
6	Comparison of memory effect with voltage or current charging pulse bias in MIS structures based on codoped Si-NCs embedded in SiO2 or HfOx. Solid-State Electronics, 2019, 159, 157-164.	1.4	2
7	Memory effect in MIS structures with embedded all-inorganic colloidal silicon carbide (SiC) nanocrystals. , 2019, , .		0
8	Stressâ€andâ€Sense Investigation of Memory Effect in Siâ€NCs MIS Structures. Physica Status Solidi (B): Basic Research, 2018, 255, 1700634.	1.5	2
9	Investigation of memory effect with voltage or current charging pulse bias in MIS structures based on codoped Si-NCs. , 2018, , .		0
10	Simulations of transient processes and characteristics of the nc-MOS structures. Microelectronic Engineering, 2017, 178, 173-177.	2.4	2
11	Technology and characterization of MIS structures with co-doped silicon nanocrystals (Si-NCs) embedded in hafnium oxide (HfOx) ultra-thin layers. Microelectronic Engineering, 2017, 178, 298-303.	2.4	9
12	Effect of nanocrystal geometric location on tunnel currents and smallâ€signal admittance of MIS structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2016, 13, 1035-1039.	0.8	3
13	Effect of interface traps parameters on admittance characteristics of the MIS (metal-insulator-semiconductor) tunnel structures. Proceedings of SPIE, 2016, , .	0.8	0
14	Small-signal admittance model of multi-traps distributed over energy and space in the insulator of MIS tunnel structures. Microelectronic Engineering, 2015, 147, 349-353.	2.4	6
15	Study of the effect of tunneling through the traps inside the insulator on small-signal admittance of the MOS structure. Microelectronic Engineering, 2013, 109, 1-4.	2.4	2
16	Investigation of current-voltage characteristics of the transistor structures with double-potential barrier DBMOS. , 2013, , .		0
17	Investigation of temperature effect on electrical characteristics of the double barrier metal-oxide-semiconductor structure. , 2013, , .		0
18	WKB approximation based formula for tunneling probability through a multi-layer potential barrier. , 2012, , .		1

#	Article	IF	Citations
19	Some Issues of Modeling the Double Barrier Metal-Oxide-Semiconductor Tunnel Structures. Advanced Materials Research, 2011, 276, 77-85.	0.3	4